

HM9N90

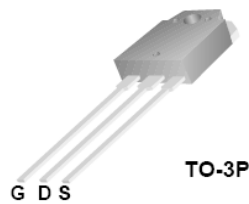
900V N-Channel MOSFET

General Description

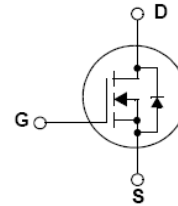
This Power MOSFET is produced using SL semi's advanced planar stripe DMOS technology. This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficiency switched mode power supplies, active power factor correction based on half bridge topology.

Features

- 9.0A, 900V, $R_{DS(on)} = 1.40\Omega @ V_{GS} = 10V$
- Low gate charge (typical 45nC)
- High ruggedness
- Fast switching
- 100% avalanche tested
- Improved dv/dt capability



TO-3P



Absolute Maximum Ratings T_C = 25°C unless otherwise noted

Symbol	Parameter	HM9N90	Units
V _{DSS}	Drain-Source Voltage	900	V
I _D	Drain Current - Continuous (T _C = 25°C)	9.0	A
	- Continuous (T _C = 100°C)	5.7	A
I _{DM}	Drain Current - Pulsed (Note 1)	36	A
V _{GSS}	Gate-Source Voltage	± 30	V
E _{AS}	Single Pulsed Avalanche Energy (Note 2)	900	mJ
E _{AR}	Repetitive Avalanche Energy (Note 1)	28	mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)	4.0	V/ns
P _D	Power Dissipation (T _C = 25°C)	280	W
	- Derate above 25°C	2.22	W/°C
T _J , T _{STG}	Operating and Storage Temperature Range	-55 to +150	°C
T _L	Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds	300	°C

* Drain current limited by maximum junction temperature.

Thermal Characteristics

Symbol	Parameter	TYP	MAX	Units
R _{θJC}	Thermal Resistance, Junction-to-Case	-	0.45	°C/W
R _{θCS}	Thermal Resistance, Case-to-Sink Typ.	0.24	-	°C/W
R _{θJA}	Thermal Resistance, Junction-to-Ambient	-	40	°C/W

Electrical Characteristics

$T_C = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
Off Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_D = 250\ \mu\text{A}$	900	--	--	V
$\Delta BV_{DSS} / \Delta T_J$	Breakdown Voltage Temperature Coefficient	$I_D = 250\ \mu\text{A}$, Referenced to 25°C	--	0.99	--	$\text{V}/^\circ\text{C}$
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 900\text{ V}, V_{GS} = 0\text{ V}$	--	--	10	μA
		$V_{DS} = 720\text{ V}, T_C = 125^\circ\text{C}$	--	--	100	μA
I_{GSSF}	Gate-Body Leakage Current, Forward	$V_{GS} = 30\text{ V}, V_{DS} = 0\text{ V}$	--	--	100	nA
I_{GSSR}	Gate-Body Leakage Current, Reverse	$V_{GS} = -30\text{ V}, V_{DS} = 0\text{ V}$	--	--	-100	nA

On Characteristics

$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\ \mu\text{A}$	2.0	--	4.0	V
$R_{DS(on)}$	Static Drain-Source On-Resistance	$V_{GS} = 10\text{ V}, I_D = 4.5\text{ A}$	--	1.05	1.40	Ω

Dynamic Characteristics

C_{iss}	Input Capacitance	$V_{DS} = 25\text{ V}, V_{GS} = 0\text{ V},$ $f = 1.0\text{ MHz}$	--	2200	--	pF
C_{oss}	Output Capacitance		--	180	--	pF
C_{rss}	Reverse Transfer Capacitance		--	15	--	pF

Switching Characteristics

$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 450\text{ V}, I_D = 9.0\text{ A},$ $R_G = 25\ \Omega$	--	50	--	ns	
t_r	Turn-On Rise Time		--	120	--	ns	
$t_{d(off)}$	Turn-Off Delay Time		(Note 4, 5)	--	100	--	ns
t_f	Turn-Off Fall Time		(Note 4, 5)	--	80	--	ns
Q_g	Total Gate Charge	$V_{DS} = 720\text{ V}, I_D = 9.0\text{ A},$ $V_{GS} = 10\text{ V}$	--	45	-	nC	
Q_{gs}	Gate-Source Charge		(Note 4, 5)	--	14	--	nC
Q_{gd}	Gate-Drain Charge		(Note 4, 5)	--	18	--	nC

Drain-Source Diode Characteristics and Maximum Ratings

I_S	Maximum Continuous Drain-Source Diode Forward Current	--	--	9.0	A	
I_{SM}	Maximum Pulsed Drain-Source Diode Forward Current	--	--	36.0	A	
V_{SD}	Drain-Source Diode Forward Voltage	$V_{GS} = 0\text{ V}, I_S = 9.0\text{ A}$	--	--	1.5	V
t_{rr}	Reverse Recovery Time	$V_{GS} = 0\text{ V}, I_S = 9.0\text{ A},$	--	550	--	ns
Q_{rr}	Reverse Recovery Charge	$di_F / dt = 100\text{ A}/\mu\text{s}$ (Note 4)	--	6.5	--	μC

Notes:

1. Repetitive Rating : Pulse width limited by maximum junction temperature
2. $L = 21.0\text{ mH}, I_{AS} = 9.0\text{ A}, V_{DD} = 50\text{ V}, R_G = 25\ \Omega$, Starting $T_J = 25^\circ\text{C}$
3. $I_{SD} \leq 9.0\text{ A}, di/dt \leq 200\text{ A}/\mu\text{s}, V_{DD} \leq BV_{DSS}$, Starting $T_J = 25^\circ\text{C}$
4. Pulse Test : Pulse width $\leq 300\ \mu\text{s}$, Duty cycle $\leq 2\%$
5. Essentially independent of operating temperature

Typical Characteristics

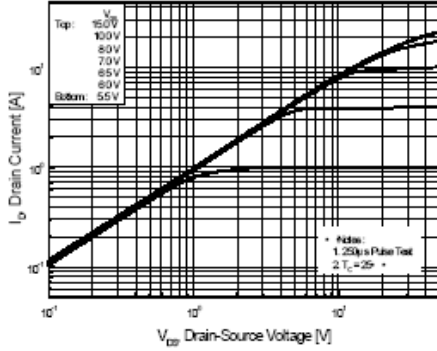


Figure 1. On-Region Characteristics

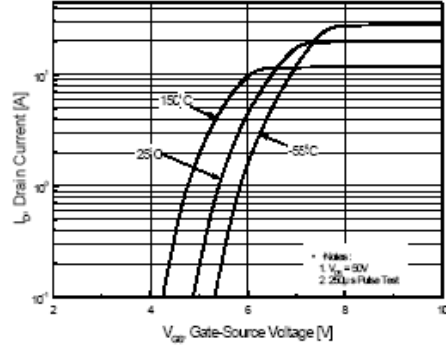


Figure 2. Transfer Characteristics

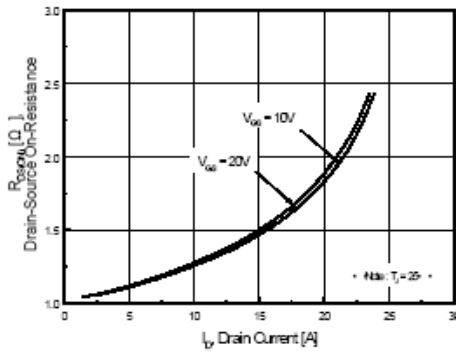


Figure 3. On-Resistance Variation vs Drain Current and Gate Voltage

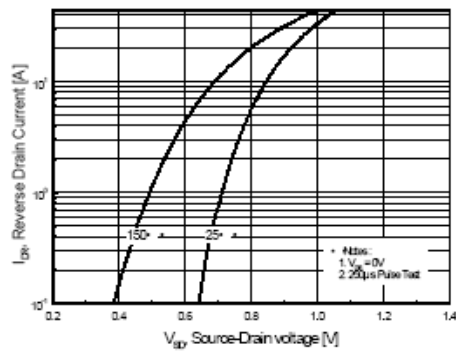


Figure 4. Body Diode Forward Voltage Variation with Source Current and Temperature

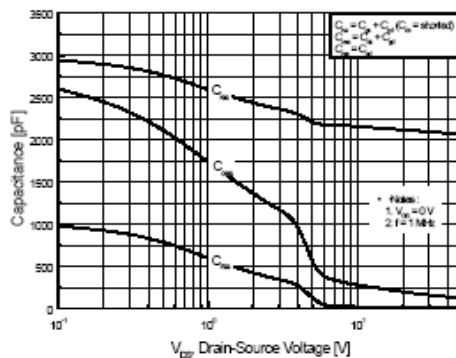


Figure 5. Capacitance Characteristics

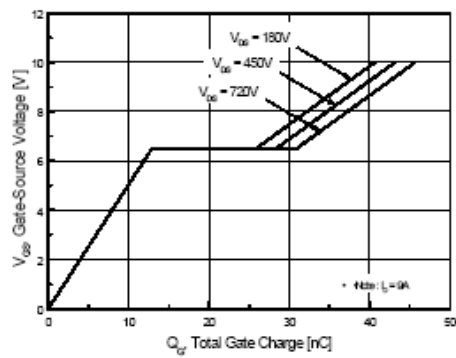


Figure 6. Gate Charge Characteristics

Typical Characteristics (Continued)

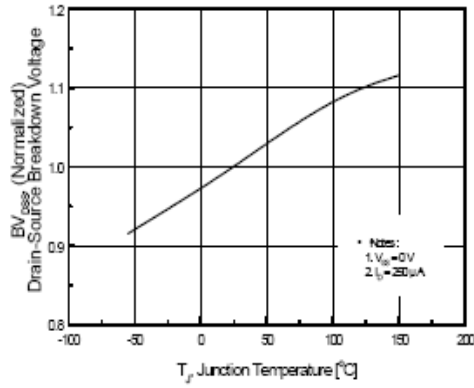


Figure 7. Breakdown Voltage Variation vs Temperature

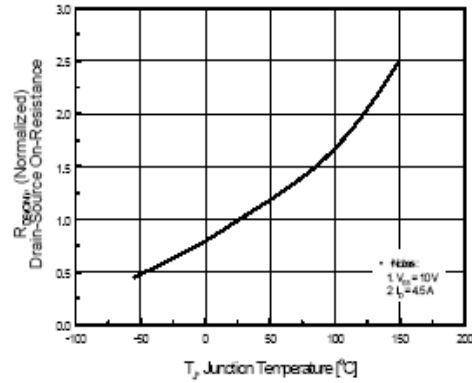


Figure 8. On-Resistance Variation vs Temperature

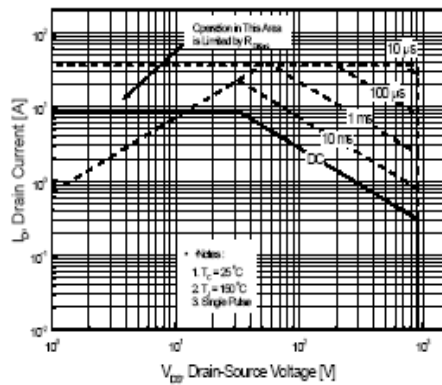


Figure 9. Maximum Safe Operating Area

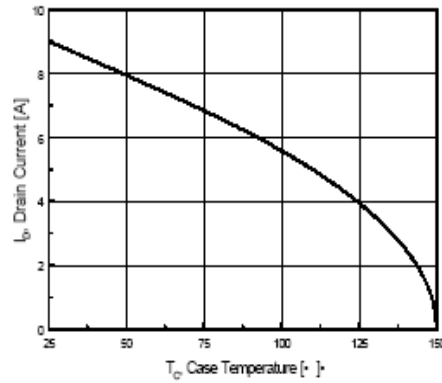


Figure 10. Maximum Drain Current vs Case Temperature

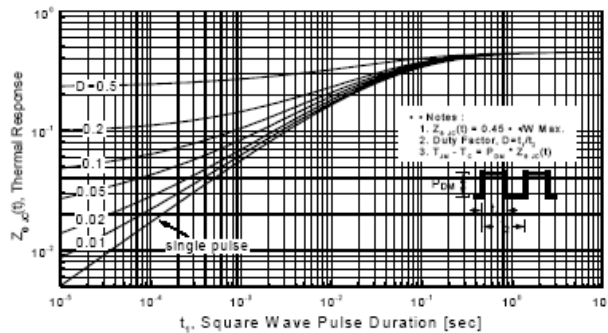
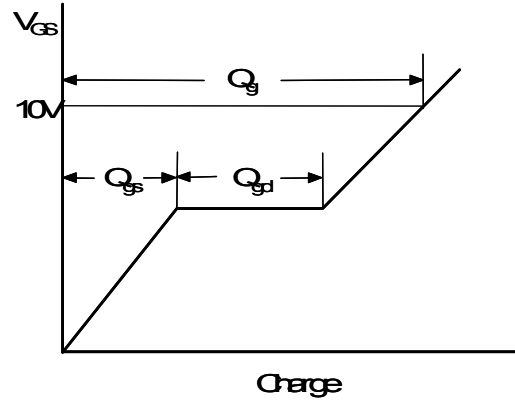
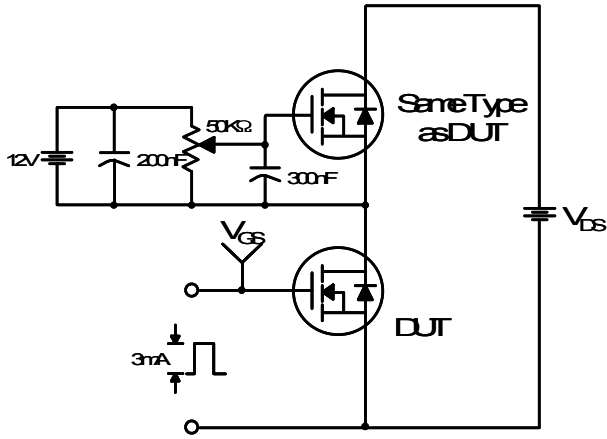
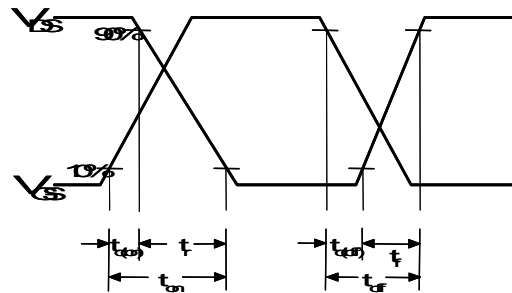
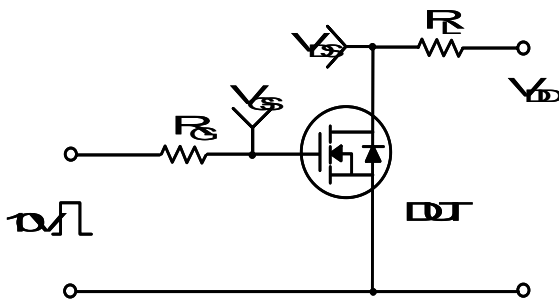


Figure 11. Transient Thermal Response Curve

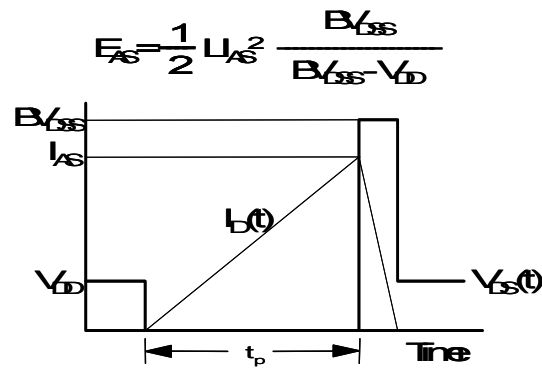
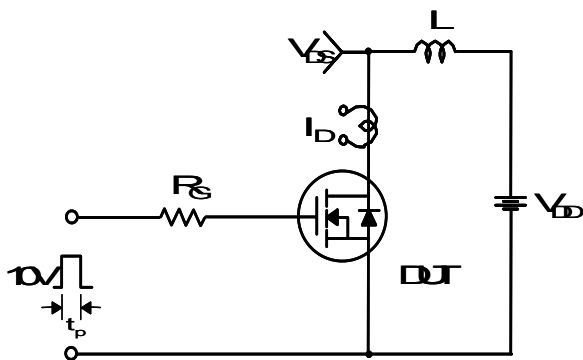
Gate Charge Test Circuit & Waveform



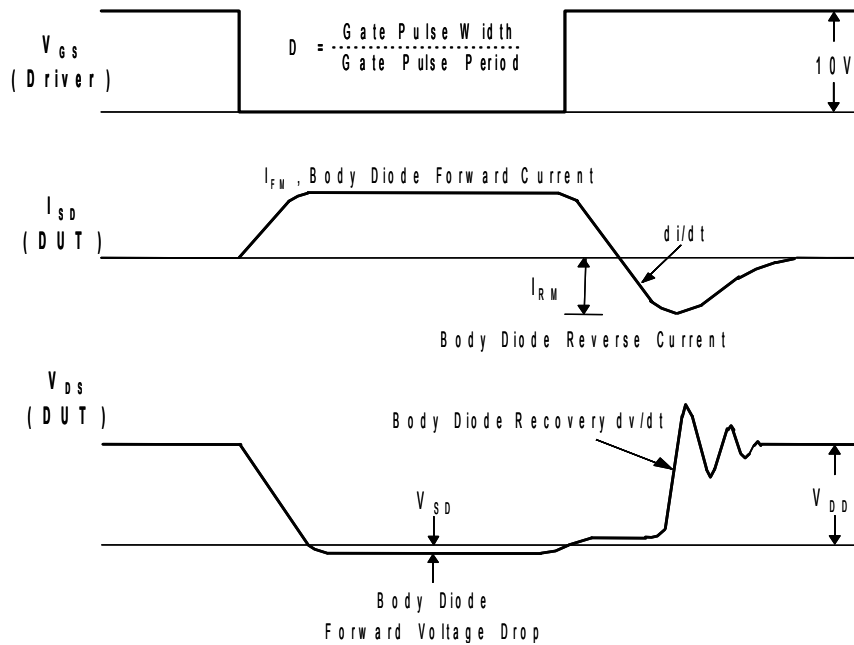
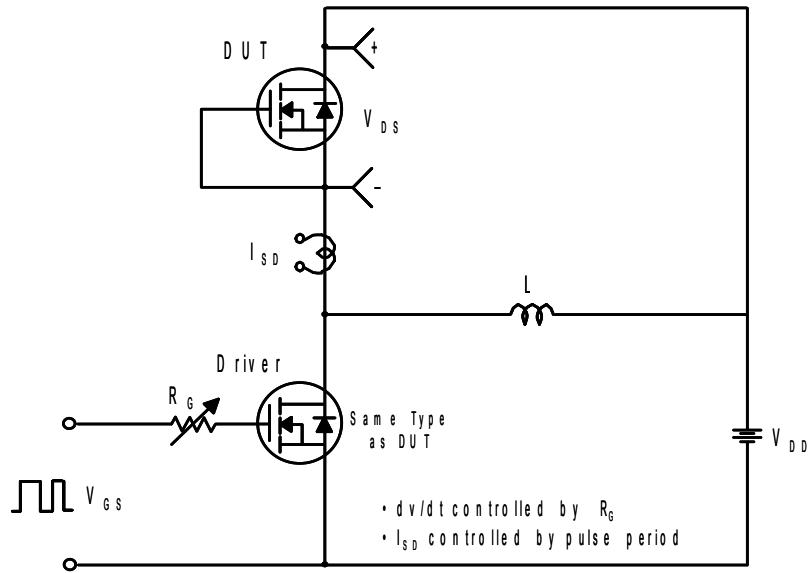
Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching Test Circuit & Waveforms

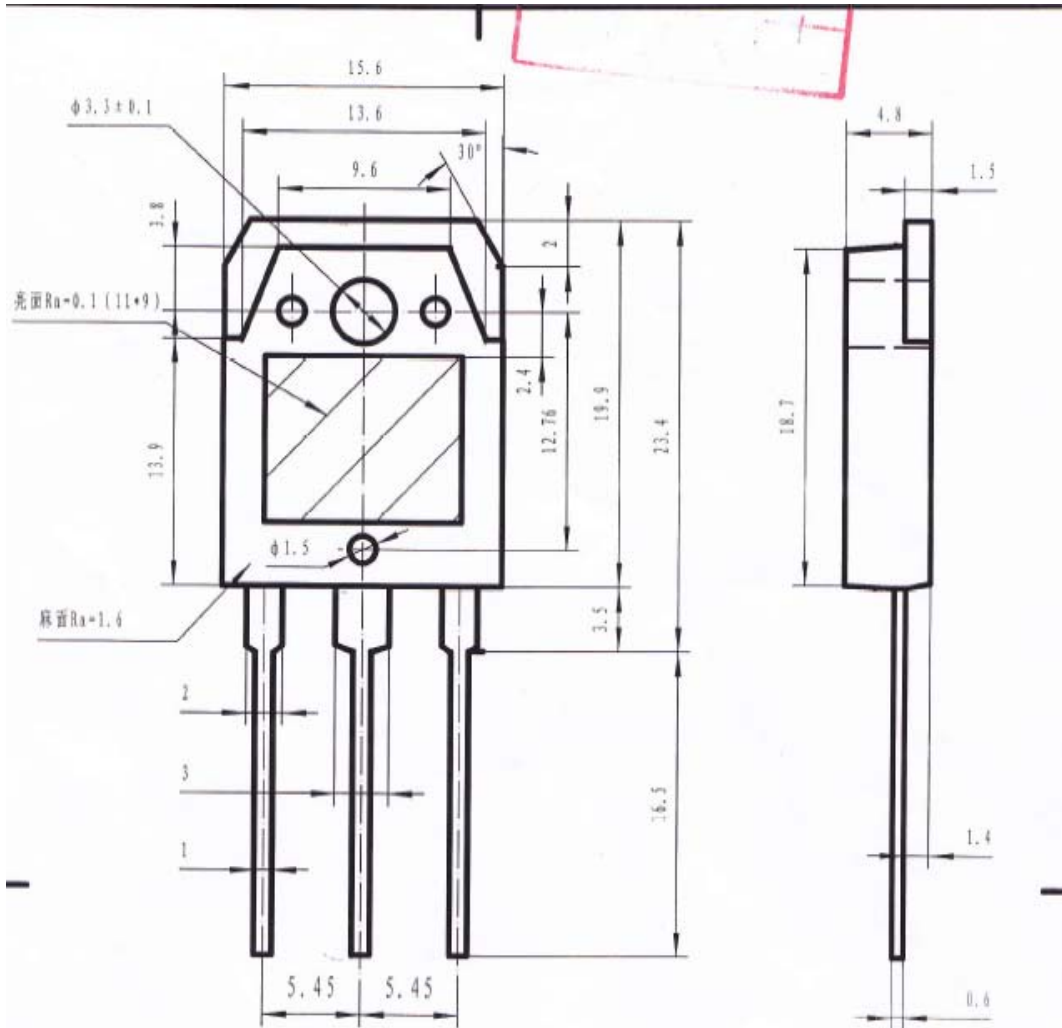


Peak Diode Recovery dv/dt Test Circuit & Waveforms



Package Dimensions

TO-3P



技术要求:

- 1 所有拔模斜度要求5度
- 2 未标注面要求成型后表面 $Ra=0.2$
- 3 未注明公差要求 $\pm 0.1mm$
- 4 树脂体不准有缺根、缩孔、裂纹、气泡等有害缺陷

